

**Amendments to the Claims:**

This Listing of Claims will replace all prior versions, and listings, of claims in the application, and remain the only claims pending in this application.

**Listing of Claims:**

Claims 1 – 34 (cancelled). **Please cancel Claims 1 – 34** and add the following new claims:

35. (new) A circuitized substrate comprising:

a first dielectric layer including an epoxy resin material and a filler comprised of particles having a size within the range of from about 200 Angstroms to about 35 microns, said particles comprising from about 10 percent to about 80 percent by volume of said first dielectric layer, said first dielectric layer not including continuous fibers, semi-continuous fibers or the like as part thereof, said first dielectric layer including a plurality of conductive thru-holes therein having a pattern density of from about 5,000 to about 10,000 holes per square inch of said first dielectric layer, said first dielectric layer having a dielectric constant within the range of from about 3.5 to about 4.0; and

at least one circuitized layer positioned on said first dielectric layer.

36. (new) The circuitized substrate of claim 35 wherein said epoxy resin of said first dielectric layer is a high glass transition temperature, dicyandiamide-free epoxy resin.

37. (new) The circuitized substrate of claim 36 wherein said first dielectric layer further includes a high molecular weight thermoplastic resin.

38. (new) The circuitized substrate of claim 35 wherein said particles of said filler comprise about 39 percent by volume of said first dielectric layer.
39. (new) The circuitized substrate of claim 35 wherein the aspect ratio of the thickness of said circuitized substrate to the diameter of each of said thru-holes being within the range of from about 2:1 to about 20:1.
40. (new) The circuitized substrate of claim 35 wherein said filler comprised of said particles comprises spherical amorphous silica having a particle size of from about 2 to about 15 microns.
41. (new) The circuitized substrate of claim 35 wherein said filler comprised of said particles comprises aluminum oxide or aluminum nitride having a particle size of from about 2 to about 15 microns.
42. (new) The circuitized substrate of claim 35 wherein said particles include a coupling agent thereon having a thickness of no more than a few monolayers.
43. (new) The circuitized substrate of claim 42 wherein said coupling agent is silane.
44. (new) The circuitized substrate of claim 35 wherein said first dielectric layer further includes a thixotrope.
45. (new) The circuitized substrate of claim 35 wherein said at least one circuitized layer is comprised of copper.

46. (new) The circuitized substrate of claim 45 further including a second circuitized layer positioned on said first dielectric layer on a side opposite said at least one circuitized layer.
47. (new) The circuitized substrate of claim 46 wherein selected ones of said conductive thru holes electrically couple selected parts of said at least one circuitized layer to selected parts of said second circuitized layer.
48. (new) The invention of claim 47 wherein said circuitized substrate comprises a chip carrier.
49. (new) The circuitized substrate of claim 47 further including second and third dielectric layers positioned on said at least one circuitized layer and said second circuitized layer, respectively, and third and fourth circuitized layers formed on said second and third dielectric layer, respectively.